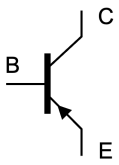
GOOD-ARK
SEMICONDUCTOR

MJ15004
PNP Power Transistor

Features

- High DC current gain - h_{FE}=25 (Min) @ I_C=-5A
- Wide area of safe operation
- Complement to the NPN MJ15003
- Minimum lot-to-lot variations for robust device performance and reliable operation

TO-3



Schematic Diagram

Applications

Designed for high power audio,disk head positioners and other linear applications.

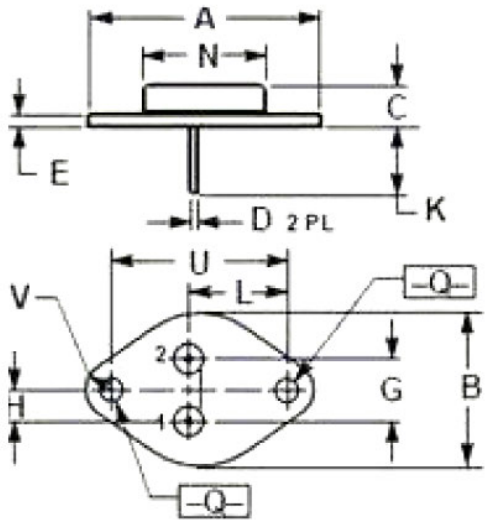
Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-140	V
Collector-Emitter Voltage	V_{CEO}	-140	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-20	A
Base Current - Continuous	I_B	-5	A
Total Power Dissipation @ T_C=25℃	P_D	250	W
Junction Temperature	T_J	200	℃
Storage Temperature Range	T_{STG}	-65 to 200	℃
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	0.7 (Max)	℃/W

Electrical Characteristics (T_C C unless other ise noted)

Parameter	Symbol	Conditions	Min	Max	Unit
Collector-Emitter Sustaining Voltage	**$V_{CEO(SUS)}$**	**I_C=-10mA, I_B=0**	**-140**	**-**	**V**
Collector-Emitter Saturation Voltage	**$V_{CE(sat)}$**	**I_C=-5A, I_B=-0.5A**	**-**	**-1**	**V**
Base-Emitter On Voltage	**$V_{BE(on)}$**	**I_C=-5A, V_{CE}=-2V**	**-**	**-2**	**V**
Collector Cutoff Current	**I_{CEO}**	**V_{CE}=-140V, I_B=0**	**-**	**-0.25**	**mA**
Collector Cutoff Current	**I_{CBO}**	**V_{CB}=-140V, I_E=0** **V_{CB}=-140V, I_E=0, T_C=150℃**			

Package Outline Dimensions (TO-3)



PIN
1. Base
2. Emitter
3. Collector(Case)

Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	39.00 Typ		1.535 Typ	
B	25.30	26.67	0.996	1.050
C	7.80	8.50	0.307	0.335
D	0.90	1.10	0.035	0.043
E	1.40	1.60	0.055	0.063
G	10.92 Typ		0.430 Typ	
H	5.46 Typ		0.215 Typ	
K	11.30	13.50	0.445	0.531
L	16.75	17.05	0.659	0.671
N	19.40	19.62	0.764	0.772
Q	4.00	4.20	0.157	0.165
U	30.00	30.20	1.181	1.189
V	4.30	4.50	0.169	0.177